

BC857BS

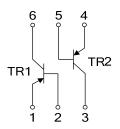
PNP SILICON TRANSISTOR

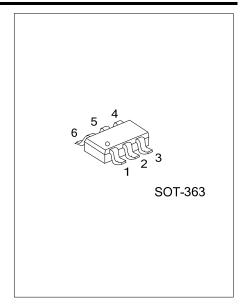
SWITCHING AND AMPLIFIER APPLICATIONS

FEATURES

*Suitable for automatic insertion in thick and thin-film circuits *Complement to BC847BS

EQUIVALENT CIRCUIT





ORDERING INFORMATION

			-i						t
Ordering Number		Package		Pin Assignment				Packing	
Lead Free	Halogen Free	T deltage	1	2	3	4	5	6	T denting
BC857BSL-AL6-R	BC857BSG-AL6-R	SOT-363	E1	B1	C2	E2	B2	C1	Tape Reel
Note: Pin Assignment: G:	: Gate D: Drain S: Sour	се							
BC857BSG-ALC	(1) R: Ta								
	(2)Package Type	e (2) AL6: SOT-363							
	(3)Green Packag	e (3) G: Ha	G: Halogen Free and Lead Free, L: Lead F				ad Free		
	ead Free Halogen Free ic Technologies Co., Ltd	JEFT EN FLY	下 「 」 「 」	FR.	12.00	[詞 cor	n		
<u>www.unisonic.com.tw</u> Copyright © 2017 Uniso <u>n</u>	ic Technologies Co., Ltd								1 of 3 QW-R206-111.

■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
Collector-Base Voltage	V _{CBO}	-50	V	
Collector-Emitter Voltage	V _{CEO}	-45	V	
Emitter-Base Voltage	V _{EBO}	-5	V	
Collector Dissipation	PD	200	mW	
Collector Current (DC)	lc	-100	mA	
Junction Temperature	T _J +150		°C	
Storage Temperature	T _{STG}	-40 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

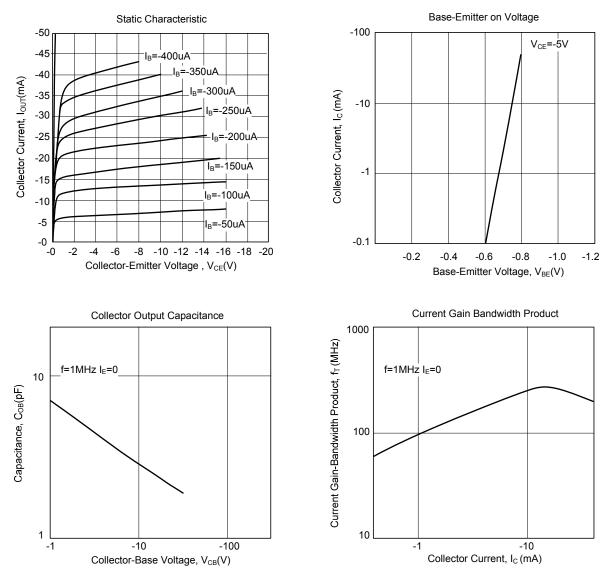
PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
Collector Cut-Off Current	I _{CBO}	V _{CB} =-30V, I _E =0			-15	nA
DC Current Gain	h _{FE}	V _{CE} =-5V, I _C =-2mA			450	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-10mA,I _B =-0.5mA			-100	mV
		I _C =-100mA,I _B =-5mA			-400	mV
Base-Emitter Saturation Voltage	$V_{\text{BE(SAT)}}$	I _C =-10mA,I _B =-0.5mA		-700		mV
		I _C =-100mA,I _B =-5mA		-900		mV
Base-Emitter On Voltage		V _{CE} =-5V,I _C =-2mA	-600	-660	-750	mV
		V _{CE} =-5V,I _C =-10mA			-800	mV
Current Gain Bandwidth Product	f _T	V _{CE} =-5V,I _C =-10mA, f=100MHz		150		MHz
Output Capacitance	Cob	V _{CB} =-10V,I _E =0,f=1MHz			6	pF
Noise Figure	NF	V _{CE} =-5V, I _C =-200μA, f=1KHz, R _G =2KΩ		2	10	dB

UNISONIC TECHNOLOGIES CO., LTD www.unisonic.com.tw

BC857BS

PNP SILICON TRANSISTOR

TYPICAL CHARACTERISTICS



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

